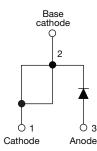


**Vishay Semiconductors** 

# HEXFRED<sup>®</sup>, Ultrafast Soft Recovery Diode, 6 A



#### TO-247AC modified



PRODUCT SUMMARY						
Package TO-247AC modified (2)						
I <sub>F(AV)</sub>	6 A					
V <sub>R</sub>	1200 V					
V <sub>F</sub> at I <sub>F</sub>	2.4 V					
t <sub>rr</sub> typ.	26 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Single die					

### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

### DESCRIPTION

VS-HFA06PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RBM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06PB120 ... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		1200	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	6			
Single pulse forward current	I <sub>FSM</sub>		80	А		
Maximum repetitive forward current	I <sub>FRM</sub>		24			
Maximum namer dissinction	P <sub>D</sub>	T <sub>C</sub> = 25 °C	62.5	W		
Maximum power dissipation		T <sub>C</sub> = 100 °C	25	vv		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

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RoHS

COMPLIANT

HALOGEN

FREE



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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \ ^{\circ}C$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-		
Maximum forward voltage		I <sub>F</sub> = 6.0 A	-	2.7	3.0	v	
	$V_{FM}$	I <sub>F</sub> = 12 A	-	3.5	3.9		
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 125 °C	-	2.4	2.8		
Maximum reverse		$V_R = V_R$ rated	-	0.26	5.0		
leakage current	IRM	$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	-	110	500	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	9.0	14	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_c = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt = 200	A/ $\mu$ s, V <sub>R</sub> = 30 V	-	26	-	
Reverse recovery time	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	53	80	ns
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 6.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	87	130	
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.4	8.0	A
	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	5.0	9.0	
	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	116	320	nC
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	233	585	ne
Peak rate of recovery current during $t_{\rm b}$	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	180	-	Δ/μο
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	100	-	A∕µs

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	2.0		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount		-	80	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified	HFA06PB120				

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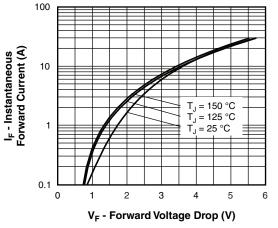
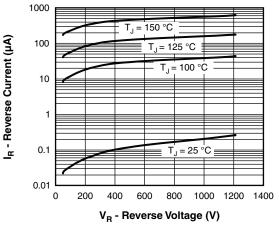
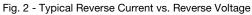


Fig. 1 - Typical Forward Voltage Drop Characteristics





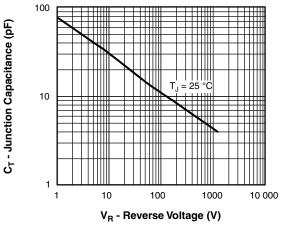


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

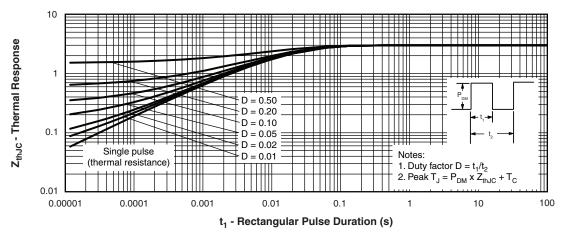


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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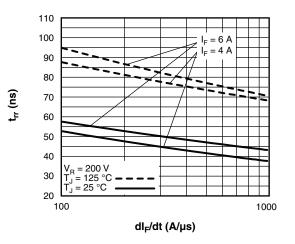


Fig. 5 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

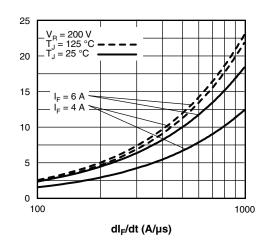


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

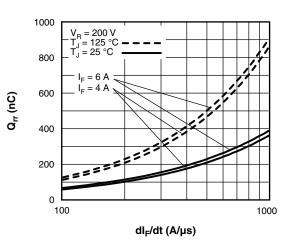
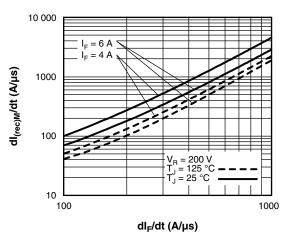


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt





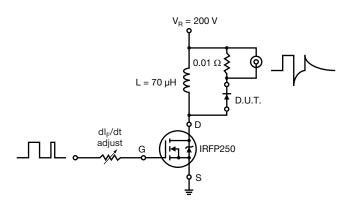


Fig. 9 - Reverse Recovery Parameter Test Circuit

I<sub>rr</sub> (A)



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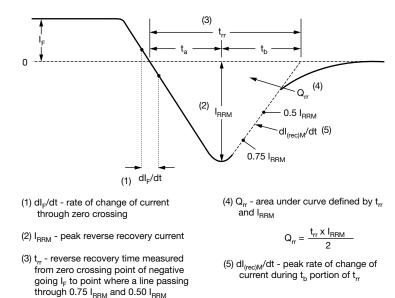
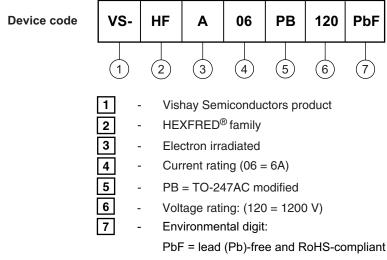


Fig. 10 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**



extrapolated to zero current.

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA06PB120PbF	25	500	Antistatic plastic tube				
VS-HFA06PB120-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95541				
	TO-247AC modified PbF	www.vishay.com/doc?95255				
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442				

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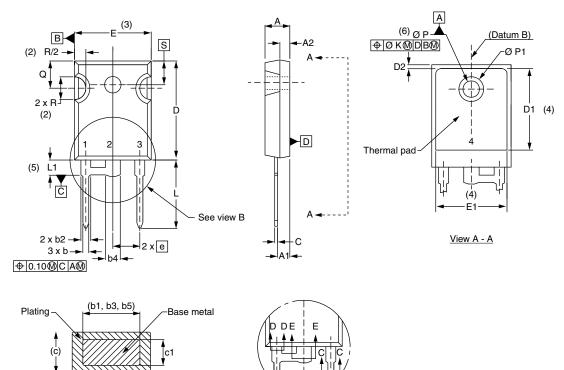
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# TO-247AC modified

### **DIMENSIONS** in millimeters and inches



Section C - C, D - D, E - E

(4)

(b. b2. b4)

View	B

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIMETERS		INCHES		NOTES
STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	-	
е	5.46 BSC		0.215	BSC	
ØК	2.54		0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	BSC	0.217 BSC		

#### Notes

- <sup>(1)</sup> Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c

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